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Vishay Semiconductors

## Thyristor Surface-Mount, Phase Control SCR, 16 A



### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub> 16 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	1600 V			
$V_{TM}$	1.25 V			
I <sub>GT</sub>	45 mA			
T <sub>J</sub>	-40 °C to +125 °C			
Package	D <sup>2</sup> PAK 2L (TO-263AB 2L)			
Circuit configuration	Single SCR			

#### **FEATURES**

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according JEDEC®-JESD 47



- Meets JESD 201 class 2 whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

### **APPLICATIONS**

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

#### **DESCRIPTION**

The VS-25TTS16S2L-M3 high voltage series of silicon controlled rectifiers is specifically designed for medium power switching and phase control applications.

#### **MECHANICAL DATA**

Case: D<sup>2</sup>PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per

J-STD-002

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS							
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5					
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	8.5	13.5	Α				
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	16.5	25.0					

#### Note

• T<sub>A</sub> = 55 °C, T<sub>J</sub> = 125 °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I <sub>T(AV)</sub>	Sinusoidal waveform	16	۸			
I <sub>RMS</sub>		25	А			
V <sub>RRM</sub> /V <sub>DRM</sub>		1600	V			
I <sub>TSM</sub>		350	A			
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V			
dV/dt		500	V/µs			
dl/dt		150	A/µs			
TJ		-40 to +125	°C			

VOLTAGE RATINGS			
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> , AT 125 °C mA
VS-25TTS16SL-M3	1600	1600	10

Revision: 25-Jan-2022 1 Document Number: 96980



ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEO	T CONDITIONS	VAL	UNITS		
PARAMETER	STINIBUL	153	I CONDITIONS	TYP. MAX.		UNITS	
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° c	onduction half sine wave	1	6		
Maximum RMS on-state current	I <sub>RMS</sub>			2	:5	А	
Maximum peak, one-cycle,	<b>L</b>	10 ms sine pulse, r	ated V <sub>RRM</sub> applied	30	00		
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, r	no voltage reapplied	3	50		
Maximum I <sup>2</sup> t for fusing	l <sup>2</sup> t	10 ms sine pulse, r	ated V <sub>RRM</sub> applied	450		A <sup>2</sup> s	
waximum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied		63	30	A-5	
Maximum $I^2\sqrt{t}$ for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied			00	A²√s	
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C			25	V	
On-state slope resistance	r <sub>t</sub>	T <sub>,1</sub> = 125 °C		2.0	mΩ		
Threshold voltage	V <sub>T(TO)</sub>	1.0		.0	V		
Maximum reverse and direct leakage current	1 /1	T <sub>J</sub> = 25 °C	V - Botad V A/	0	.5		
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$	1	0		
Holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C		-	150	mA	
Maximum latching current	IL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C 200			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = Open$		$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = Open$ 500		00	V/µs
Maximum rate of rise of turned-on current	dl/dt			150		A/µs	

TRIGGERING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum peak gate power	P <sub>GM</sub>		8.0	W			
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV			
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α			
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V			
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	60	mA			
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	45				
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	20				
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	2.5				
Maximum required DC gate voltage to trigger	V <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	.,			
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V			
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V Detect value	0.25				
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	2.0	mA			

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9			
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.I</sub> = 125 °C	4	μs		
Typical turn-off time	t <sub>q</sub>	1 1 = 125 0	110			

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C		
Soldering temperature	T <sub>S</sub>	For 10 s (1.6 mm from case)	260			
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.1	°C/W		
Typical thermal resistance, junction to ambient (PCB mount)	R <sub>thJA</sub> <sup>(1)</sup>		40	C/VV		
Approximate weight			2	g		
Approximate weight			0.07	OZ.		
Marking device		Case style D <sup>2</sup> PAK 2L (TO-263AB 2L)	25TT	S16S		

#### Note

 $<sup>^{(1)}</sup>$  When mounted on 1" square (650 mm<sup>2</sup>) PCB of FR-4 or G-10 material 4 oz. (140  $\mu$ m] copper 40 °C/W

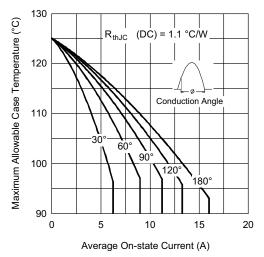


Fig. 1 - Current Rating Characteristics

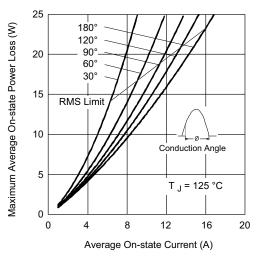
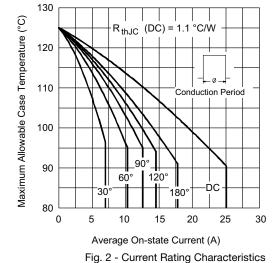


Fig. 3 - On-State Power Loss Characteristics



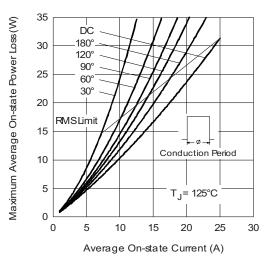


Fig. 4 - On-State Power Loss Characteristics

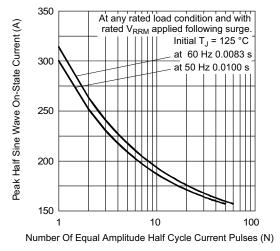


Fig. 5 - Maximum Non-Repetitive Surge Current

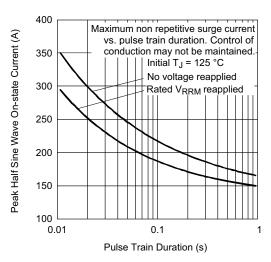


Fig. 6 - Maximum Non-Repetitive Surge Current

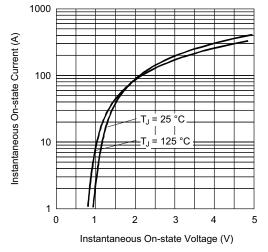


Fig. 7 - On-State Voltage Drop Characteristics

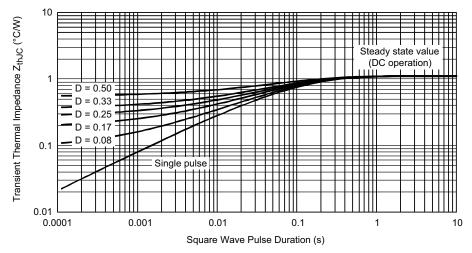


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

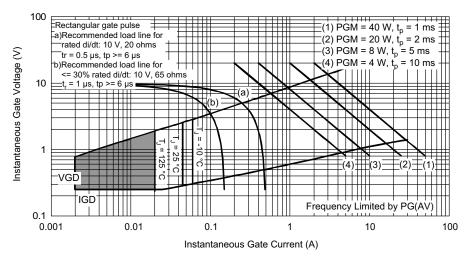


Fig. 9 - Gate Characteristics

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# ORDERING INFORMATION TABLE

Device code	VS-	25	Т	Т	s	16	s	2	L	-M3
	1	2	3	4	5	6	7	8	9	10
	Vishay Semiconductors product									
	2 -	2 - Current rating (25 = 25 A)								

Gircuit configuration:
T = single thyristor

 $\begin{array}{c|cccc} \textbf{4} & - & \text{Package:} \\ & & T = D^2 \text{PAK (TO-263AB)} \end{array}$ 

5 - Type of silicon:

S = standard recovery rectifier

6 - Voltage rating: Voltage code x 100 = V<sub>RRM</sub> — 16 = 1600 V

S = surface mountable

2 = true 2 pin D<sup>2</sup>PAK
 L = tape and reel (left oriented), for different orientation contact factory

10 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-25TTS16S2L-M3	800	800	13" diameter reel			

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?96683				
Part marking information	www.vishay.com/doc?96693			
Packaging information	www.vishay.com/doc?96317			



# **D<sup>2</sup>PAK 2L (TO-263AB 2L)**

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	IETERS	INCHES		NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
Е	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L3	0.25 BSC		0.010 BSC		
L4	4.78	5.28	0.188	0.208	

### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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